

# ABSTRACT OF THE DISCLOSURE

A silicon carbide (SiC) substrate is provided with an off-oriented {0001} surface whose off-axis direction is  $\langle 11-20 \rangle$ .

A trench is formed on the SiC to have a stripe structure  
5 extending toward a  $\langle 11-20 \rangle$  direction. An SiC epitaxial layer is formed on an inside surface of the trench.